General Purpose Transistors

NPN Silicon

Features

• Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage 2N4123 2N4124	V _{CEO}	30 25	Vdc
Collector-Base Voltage 2N4123 2N4124	V _{CBO}	40 30	Vdc
Emitter-Base Voltage	V _{EBO}	5.0	Vdc
Collector Current – Continuous	Ι _C	200	mAdc
Total Device Dissipation @ $T_A = 25^{\circ}C$ Derate above 25°C	P _D	625 5.0	mW mW/°C
Total Device Dissipation @ $T_C = 25^{\circ}C$ Derate above 25°C	PD	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

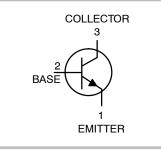
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W

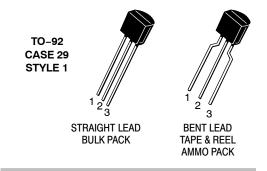
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



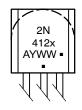
ON Semiconductor®

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MARKING DIAGRAM



x = 3 or 4 A = Assembly Location Y = Year WW = Work Week • = Pb-Free Package (Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
2N4123RLRM	TO-92	2000 / Tape & Ammo
2N4124G	TO-92 (Pb-Free)	5000 Units / Bulk

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

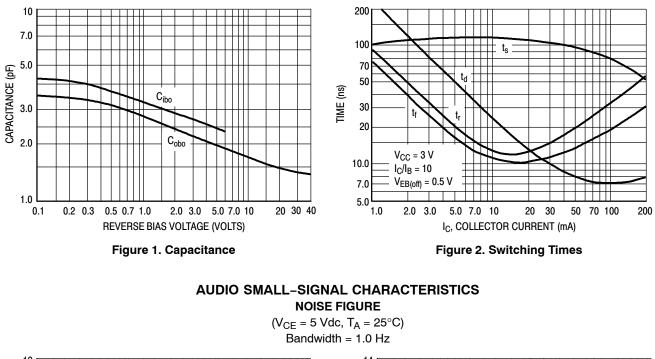
*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS			•	•	
Collector – Emitter Breakdown Voltage (Note 1) ($I_C = 1.0 \text{ mAdc}, I_E = 0$)	2N4123 2N4124	V _{(BR)CEO}	30 25		Vdc
Collector-Base Breakdown Voltage $(I_C = 10 \ \mu Adc, I_E = 0)$	2N4123 2N4124	V _{(BR)CBO}	40 30		Vdc
Emitter-Base Breakdown Voltage ($I_E = 10 \ \mu Adc, I_C = 0$)		V _{(BR)EBO}	5.0	-	Vdc
Collector Cutoff Current ($V_{CB} = 20 \text{ Vdc}, I_E = 0$)		I _{CBO}	-	50	nAdc
Emitter Cutoff Current ($V_{EB} = 3.0 \text{ Vdc}, I_C = 0$)		I _{EBO}	_	50	nAdc
ON CHARACTERISTICS			•	•	
DC Current Gain (Note 1) (I _C = 2.0 mAdc, V _{CE} = 1.0 Vdc)	2N4123 2N4124	h _{FE}	50 120	150 360	_
$(I_C = 50 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc})$	2N4123 2N4124		25 60		
Collector – Emitter Saturation Voltage (Note 1) ($I_C = 50 \text{ mAdc}, I_B = 5.0 \text{ mAdc}$)		V _{CE(sat)}	_	0.3	Vdc
Base – Emitter Saturation Voltage (Note 1) ($I_C = 50 \text{ mAdc}, I_B = 5.0 \text{ mAdc}$)		V _{BE(sat)}	_	0.95	Vdc
SMALL-SIGNAL CHARACTERISTICS			•	•	
Current-Gain – Bandwidth Product (I _C = 10 mAdc, V _{CE} = 20 Vdc, f = 100 MHz)	2N4123 2N4124	f _T	250 300		MHz
Input Capacitance $(V_{EB} = 0.5 \text{ Vdc}, I_C = 0, f = 1.0 \text{ MHz})$		C _{ibo}	-	8.0	pF
Collector-Base Capacitance $(I_E = 0, V_{CB} = 5.0 \text{ V}, f = 1.0 \text{ MHz})$		C _{cb}	_	4.0	pF
Small–Signal Current Gain (I_C = 2.0 mAdc, V_{CE} = 10 Vdc, R_S = 10 k Ω , f = 1.0 kHz)	2N4123 2N4124	h _{fe}	50 120	200 480	_
Current Gain – High Frequency (I _C = 10 mAdc, V _{CE} = 20 Vdc, f = 100 MHz)	2N4123 2N4124	h _{fe}	2.5 3.0		_
$(I_{C} = 2.0 \text{ mAdc}, V_{CE} = 10 \text{ V}, f = 1.0 \text{ kHz})$ $(I_{C} = 2.0 \text{ mAdc}, V_{CE} = 10 \text{ V}, f = 1.0 \text{ kHz})$	2N4123 2N4124		50 120	200 480	
Noise Figure (I_C = 100 μ Adc, V _{CE} = 5.0 Vdc, R _S = 1.0 k Ω , f = 1.0 kHz)	2N4123 2N4124	NF		6.0 5.0	dB

1. Pulse Test: Pulse Width = 300 μ s, Duty Cycle = 2.0%.



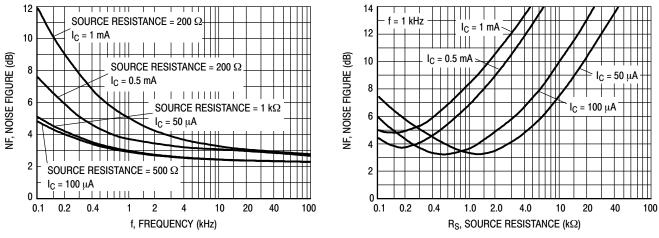
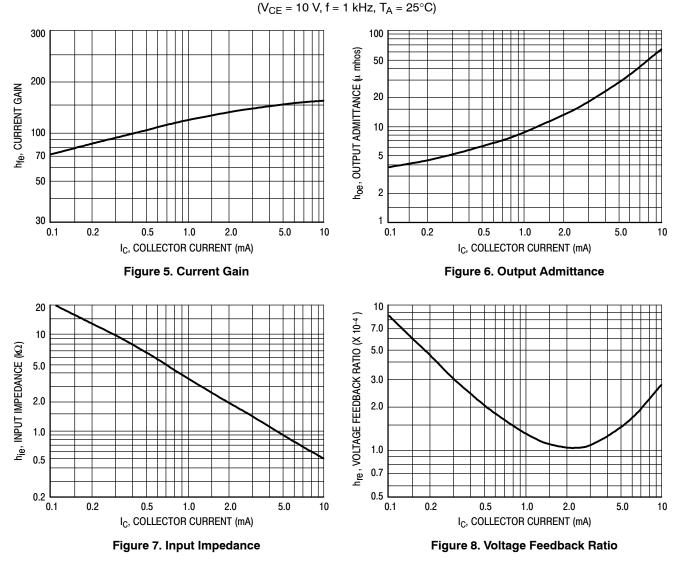
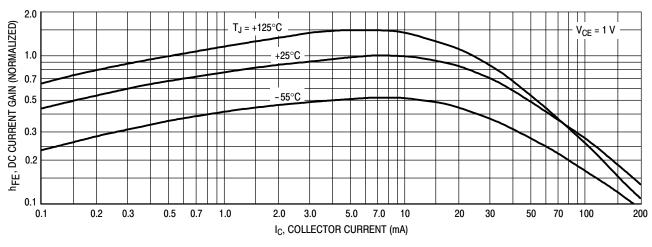


Figure 3. Frequency Variations

Figure 4. Source Resistance

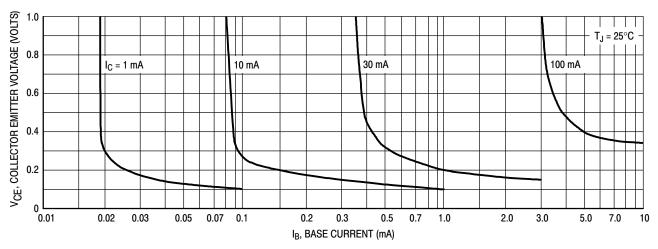
h PARAMETERS

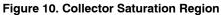


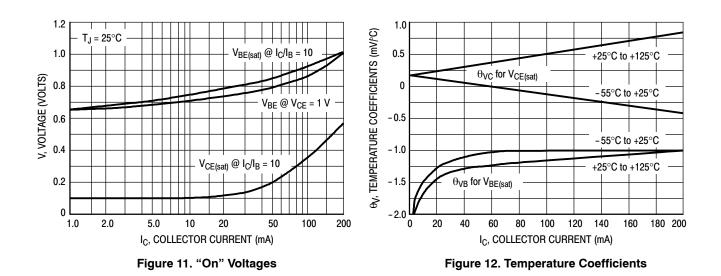


STATIC CHARACTERISTICS

Figure 9. DC Current Gain

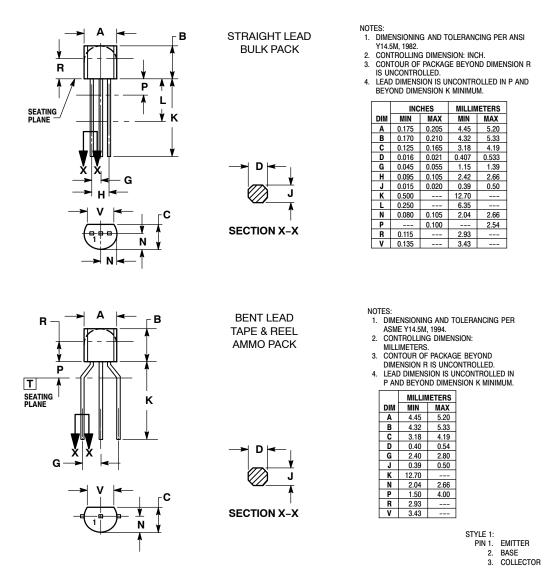






PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AM**



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